

Fig. 1 (prior art)

BEST AVAILABLE COPY

## MALABLE COPY

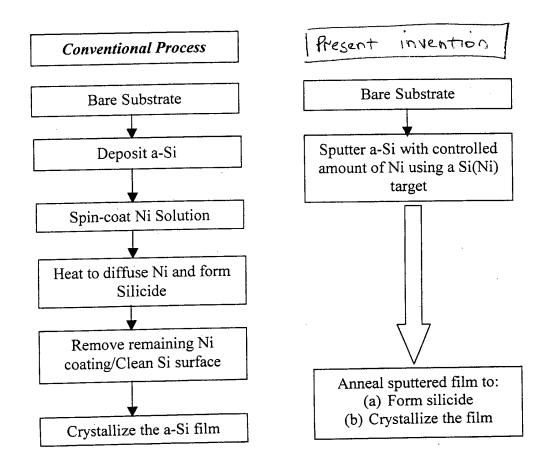


Fig. 2

| START 300                             |
|---------------------------------------|
| 302                                   |
| Forming target of Si and              |
| List importy 304                      |
| S S S S S S S S S S S S S S S S S S S |
| Supplying substrate 306               |
|                                       |
| Spotter depositing si film            |
| with lit impurity 308                 |
| 1 308                                 |
| Tannealing to form silicide           |
| 3130                                  |
| Connenting to crystalize              |
|                                       |

Fig. 3

Start Supplying Substrate forming target EEST AVAILABLE COPY sputter depositing to form silicide annealing to crystaliz

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